



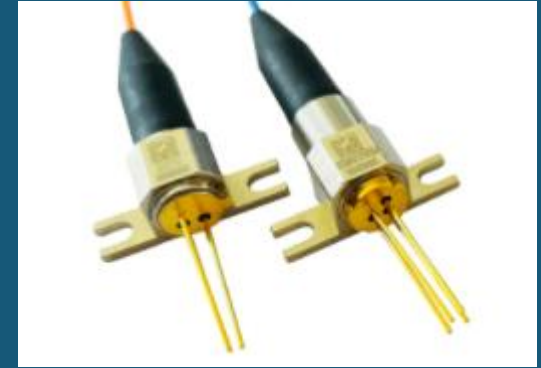
CWDM (1270nm~1610nm) DFB Pulse laser diode module

Features

- Advanced Multiple Quantum Well (MQW) laser
- Distributed Feedback (DFB) Laser Design
- Low Threshold Current
- Built-in InGaAsP monitor PD
- Cost-effective Uncooled Laser Technology
- 1 Pulse Conditions: Pulse width (PW)=10us, Duty = 1%

Application

- CATV Return-Patch
- Analog Transmission
- Light Source
- Sensor
- Optical telecommunication
- OTDR



Absolute Maximum Ratings (Tc=25°C .unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Reverse voltage (monitor PD)	V_{RM}	-	10	V	-
Reverse Voltage	V_R		2	V	CW
Operating Temperature	T_{OP}	-20	+70	°C	-
Storage Temperature	T_{stg}	-40	+100	°C	-
Soldering Temperature/Time	-	260/10		°C/S	-

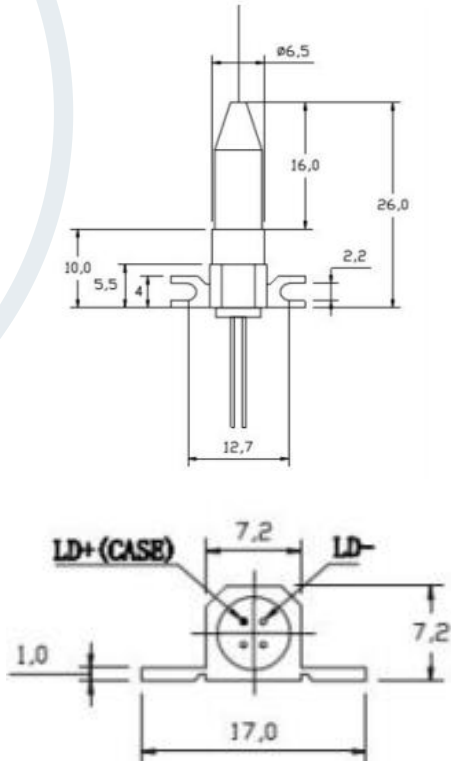


Reverse Current (monitor PD)	I_{FPM}	-	2	mA	-
Relative Humidity (non-condensing)	RH		85	%	-

Optical & electrical characteristics (Tc=25°C)

Parameter	Symbol	Min	Typ.	Max.	Unit	Test Conditions
Optical Output Power	P_o	30	-	-	mW	1270nm~1490nm, $I_{FP} \leq 250\text{mA}$, $P_w=10\mu\text{s}$, Duty= 1%
						1510nm~1610nm, $I_{FP} \leq 350\text{mA}$, $P_w=10\mu\text{s}$, Duty= 1%
Threshold Current	I_{th}	-	10	20	mA	$P_{fcw} = 2\text{mW}$, $V_{rm} = 2\text{V}$
Forward Voltage	V_F	-	-	3.5	V	$I_{FP} \leq 350\text{mA}$, $P_w=10\mu\text{s}$, Duty= 1%
Center Wavelength	λ_c	1290	1310	1330	nm	Rms (-20 dB), $I_{FP}=350\text{mA}$, $P_w=10\mu\text{s}$, Duty= 1%
		1530	1550	1570		
		λ_c-3	λ_c	λ_c+3		
Spectral Width (-20 dB)	$\Delta \lambda$	-	0.5	1	nm	CW, 25°C, $I_{th}+ 20\text{mA}$
Rise / Fall time	T_r / T_f	-	0.3	0.7	ns	CW, $I_{th}+ 20\text{mA}$
Monitor Dark Current	I_D	-	-	200	nA	$V_{rpd} = 5\text{V}$
Optical Isolation	ISO	30	-	-	dB	25°C

Dimensions(mm)



Order Information

GTA1003

“O Wavelength” 1270nm ~ 1410nm.

“S+C+L Wavelength” 1430nm ~ 1610nm.



Please let us know your request details before order.



Customize for you

